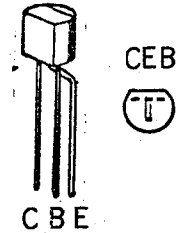


BF224 is an NPN silicon planar epitaxial transistor designed for general purpose high frequency oscillator, amplifier, and mixer applications.

CASE TO-92E



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V _{CB0}	45V
Collector-Emitter Voltage	V _{CE0}	30V
Emitter-Base Voltage	V _{EB0}	4V
Collector Current	I _C	50mA
Total Power Dissipation	P _{tot}	250mW
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS @ T_A=25°C (unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV _{CB0}	45			V	I _C =100μA I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	30			V	I _C =7mA I _B =0
Emitter-Base Breakdown Voltage	BV _{EB0}	4			V	I _E =100μA I _C =0
Collector Cutoff Current	I _{CB0}			100 10	nA μA	V _{CB} =20V I _E =0 V _{CB} =20V T _A =85°C
Emitter Cutoff Current	I _{EB0}			100	nA	V _{EB} =3V I _C =0
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.15	V	I _C =10mA I _B =1mA
Base-Emitter Voltage	V _{BE}			0.9	V	I _C =7mA V _{CB} =10V
D.C. Current Gain	H _{FE}	30				I _C =7mA V _{CE} =10V
Current Gain-Bandwidth Product	f _T	300	450 500		MHz MHz	I _C =1.5mA V _{CE} =10V I _C =7mA V _{CE} =10V
Feedback Capacitance	C _{re}		0.3		pF	I _E =1mA V _{CB} =10V f=10.7MHz



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